Features

- Super Junction High Voltage MOSFET technology
- High Density Cell Design For Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free."Green"Device(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

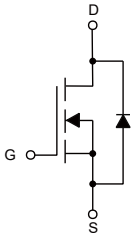
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 48°C/W Junction to Ambient(Note2)
- Thermal Resistance: 1.7°C/W Junction to Case

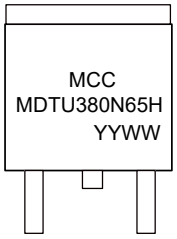
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Volltage		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	8.7	A
	T_C=100°C		5.5	
Pulsed Drain Current(Note 3)		I_{DM}	34.8	A
Total Power Dissipation(Note 4)		P_D	73	W
Single Pulsed Avalanche Energy(Note 5)		E_{AS}	93.75	mJ

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{GS}=10V, Rg=25Ω,L=30mH.

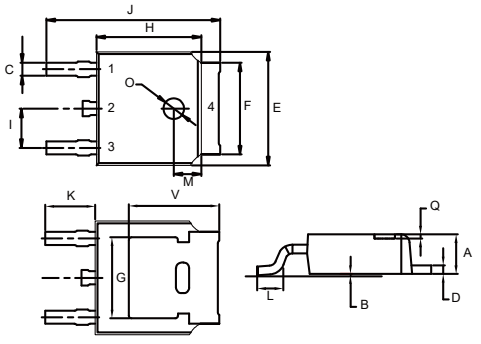
Internal Structure and Marking Code





4 codes in total
YY is the year
WW is the week

DPAK(TO-252)



1. Gate
2,4. Drain
3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	650			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±30V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.2	3.0	3.8	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=5A		300	380	mΩ
Gate Resistance	R_g	f=1 MHz, Open drain		4.0		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				11	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=8.7A		0.88	1.2	V
Reverse Recovery Time	t_{rr}	I_F=8.5A, dI_F/dt=100A/μs, V_R=325V		208		ns
Reverse Recovery Charge	Q_{rr}			2086		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=325V,V_{GS}=0V,f=1MHz		625		pF
Output Capacitance	C_{oss}			4.7		
Reverse Transfer Capacitance	C_{rss}			1.3		
Total Gate Charge	Q_g	V_{DS}=325V,V_{GS}=10V,I_D=8.5A		13.7		nC
Gate-Source Charge	Q_{gs}			3.0		
Gate-Drain Charge	Q_{gd}			5.7		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=325V, V_{GS}=10V, I_{DS}=8.5A,R_{GEN}=3Ω		30		ns
Turn-On Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(off)}$			18		
Turn-Off Fall Time	t_f			13		

Curve Characteristics

Fig.1 - Typical Output Characteristics

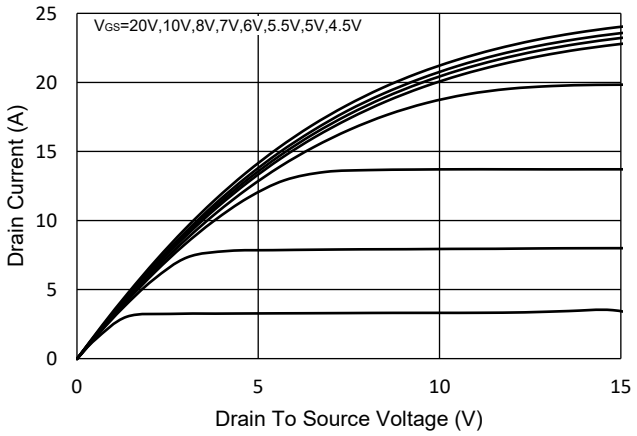


Fig.2 - Transfer Characteristics

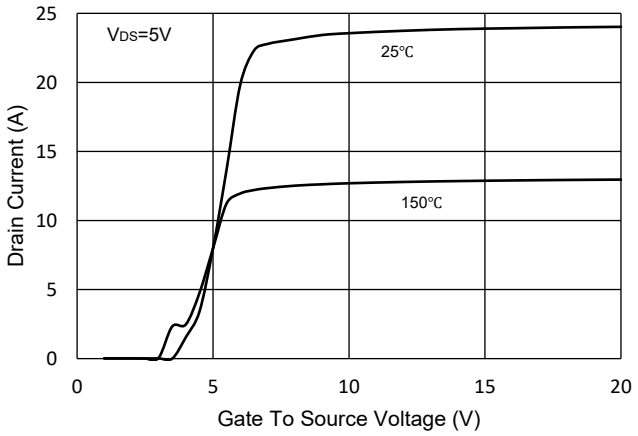


Fig.3 - $R_{DS(ON)}$ - V_{GS}

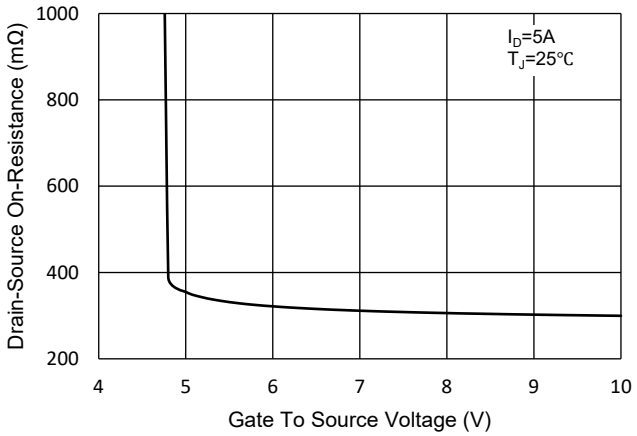


Fig.4 - $R_{DS(ON)}$ - I_D

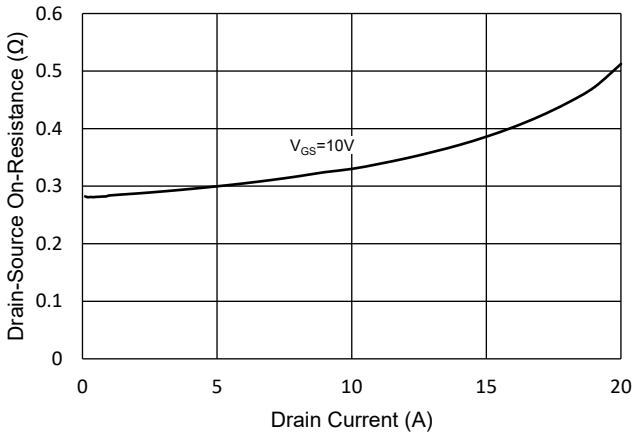


Fig.5 - Capacitance Characteristics

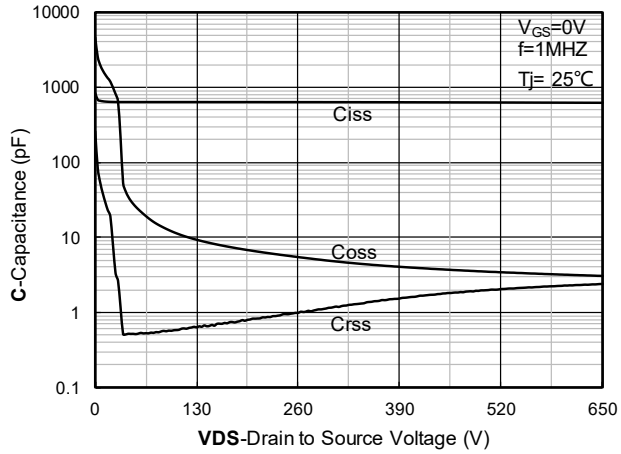
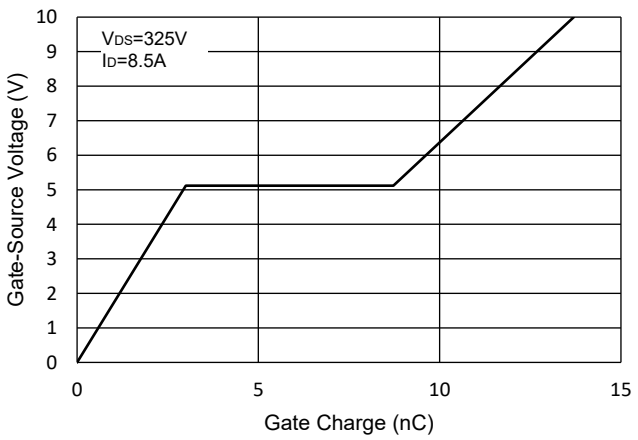


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

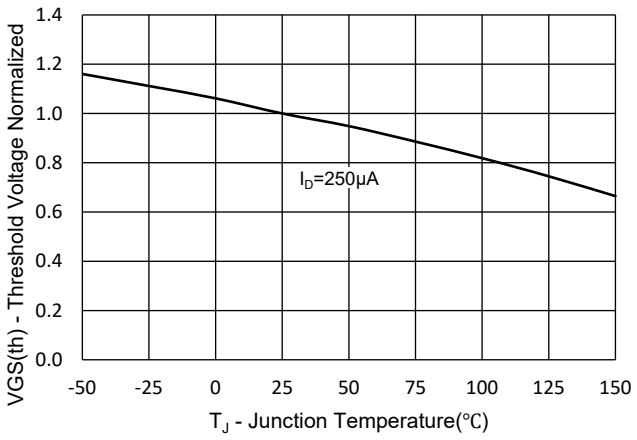


Fig.8 - Normalized On Resistance Characteristics

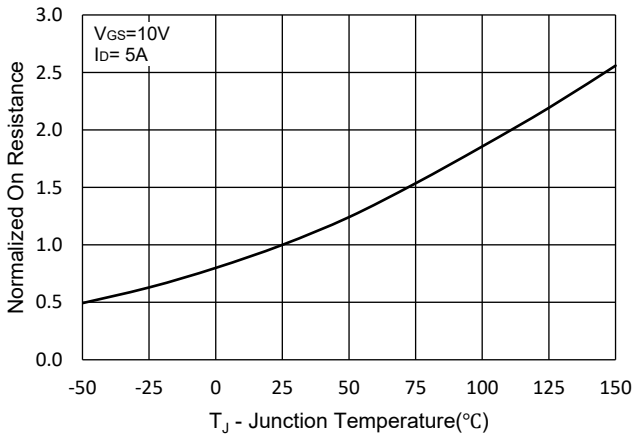


Fig.9 - I_S - V_{SD}

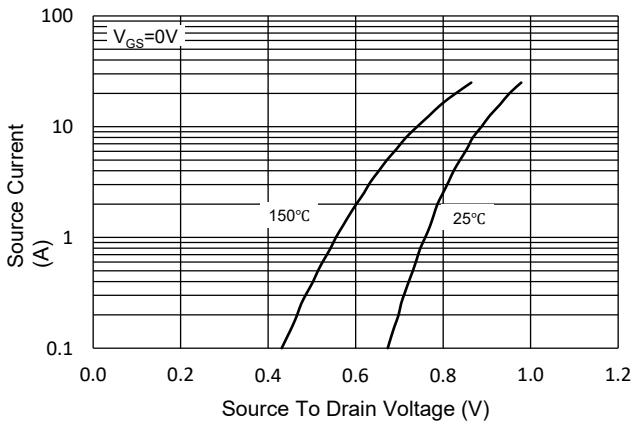


Fig.10 - Drain Current

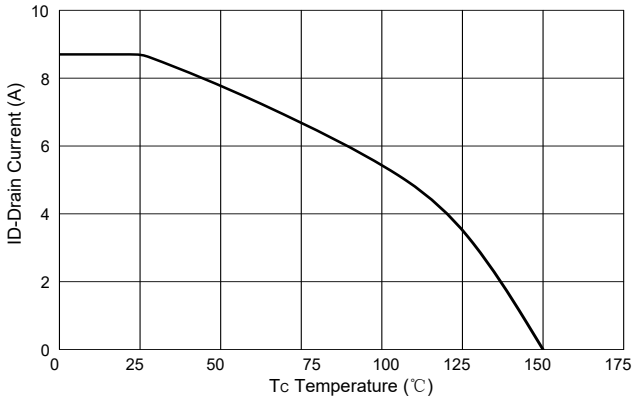
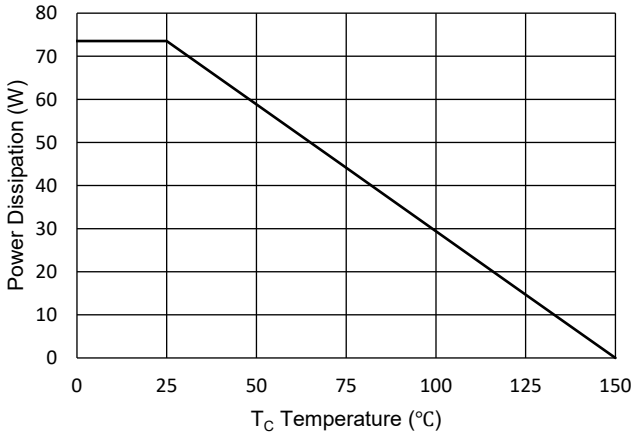


Fig.11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

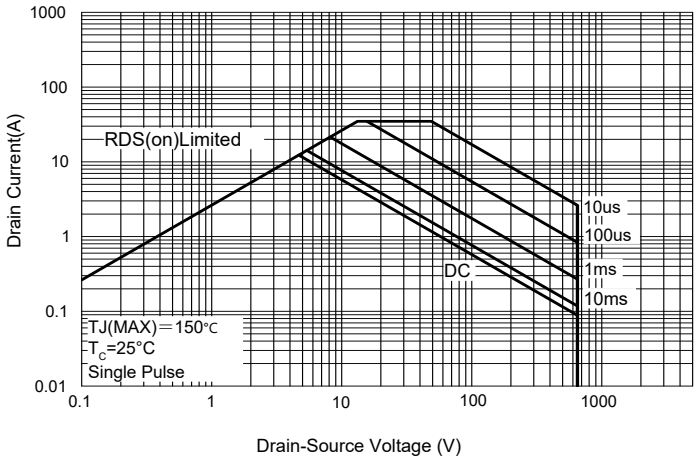
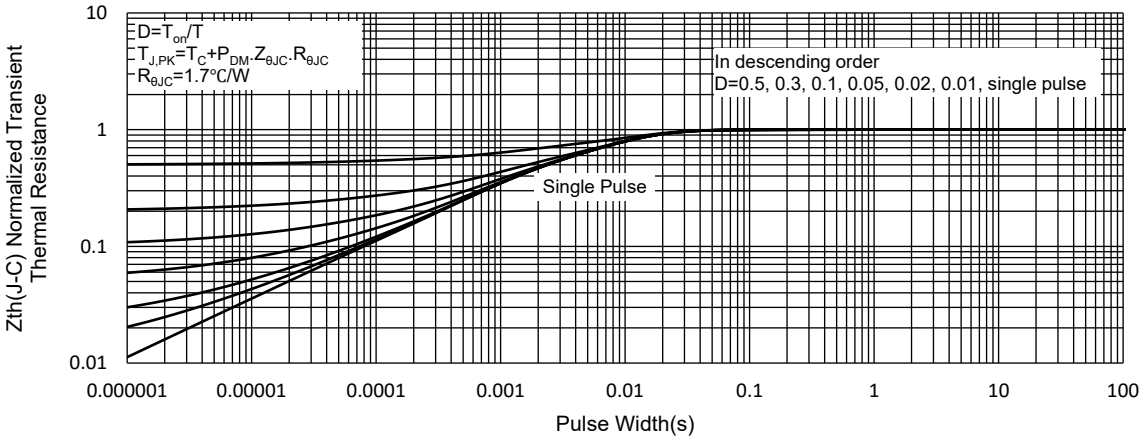


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel